
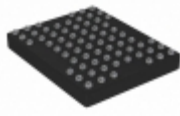

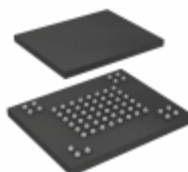


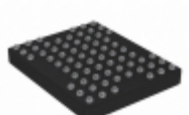


 <p>TOSHIBA Leading Innovation >>></p>	<h2 style="color: #E67E22;">TC58NVG0S3HTAI0</h2>	
	<p>Hersteller-Teilenummer: TC58NVG0S3HTAI0</p> <hr/> <p>Hersteller / Marke: Toshiba Memory America, Inc.</p> <hr/> <p>Teil der Beschreibung: IC FLASH 1G PARALLEL 48TSOP I</p> <hr/> <p>Datenblätter:  TC58NVG0S3HTAI0.pdf</p> <hr/> <p>RoHs Status: Bleifrei / RoHS-konform</p> <hr/> <p>Lagerzustand: New original, 1687 pcs Stock Available.</p> <hr/> <p>Liefern von: Hong Kong</p> <hr/> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>	
<p>Image may be representation. See specs for product details.</p>		

Spezifikationen

Teilenummer	TC58NVG0S3HTAI0
Hersteller	Toshiba Memory America, Inc.
Beschreibung	IC FLASH 1G PARALLEL 48TSOP I
Kategorie	Integrierte Schaltungen (ICs) > Erinnerung
Teilstatus	1687 pcs Stock
detaillierte Beschreibung	FLASH - NAND (SLC) Memory IC 1Gb (128M x 8)
Serie	-
Technologie	FLASH - NAND (SLC)
Betriebstemperatur	-40°C ~ 85°C (TA)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	48-TFSOP (0.724", 18.40mm Width)
Supplier Device-Gehäuse	48-TSOP I
Spannungsversorgung	2.7 V ~ 3.6 V
Speichertyp	Non-Volatile
Speichergröße	1Gb (128M x 8)
Zugriffszeit	25ns
Speicherformat	FLASH
Schreibzyklus Zeit - Wort, Seite	25ns
Speicherschnittstelle	Parallel
Verpackung	Tray
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	3 (168 Hours)
Andere Namen	TC58NVG0S3HTAI0B4H



TC58NVG0S3HTAI0 ist neu im Original, Suche TC58NVG0S3HTAI0 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie TC58NVG0S3HTAI0 Toshiba Memory America, Inc. mit Garantie und Vertrauen. Anfrage TC58NVG0S3HTAI0: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>TC58NVG0S3HBAI6 Toshiba Memory America, Inc. IC FLASH 1G PARALLEL 67VFBGA</p>	 <p>TC58NVG0S3HTA00 Toshiba Semiconductor and Storage IC EEPROM 1GBIT 25NS 48TSOP</p>	 <p>TC58NVG0S3HBAI4 Toshiba Memory America, Inc. IC FLASH 1G PARALLEL 63TFBGA</p>	 <p>TC58NVG0S3HTA00 Toshiba Memory America, Inc. IC FLASH 1G PARALLEL 48TSOP I</p>
 <p>TC58NVG1S3AFT05 Toshiba Semiconductor and Storage TC58NVG1S3AFT05 TOSHIBA</p>	 <p>TC58NVG0S3HBAI6 Toshiba Semiconductor and Storage IC EEPROM 1GBIT 25NS 67FBGA</p>	 <p>TC58NVG0S3HTAI0 Toshiba Semiconductor and Storage IC EEPROM 1GBIT 25NS 48TSOP</p>	 <p>TC58NVG0S3HTAI0B4H Toshiba Semiconductor and Storage TC58NVG0S3HTAI0B4H TOSHIBA</p>

heiße Teile

Mehr

- | | | | | |
|--|--|---|---|--|
|  TC58FVB800FT-12 |  TC58FVM5B2ATG65 |  TC58FVM5B2AXG65 |  TC58FVM5T2ATG65 |  TC58FVM6B2ATG65 |
|  TC58FVM6B5BTG65 |  TC58FVM6T5BTG65 |  TC58FVM7T5BTG65 |  TC58FVT160AFT-70 |  TC58FVT160AFT70 |
|  TC58FVT160FT-10 |  TC58FVT160FT-85 |  TC58G-315-03G |  TC58NC344AF |  TC58NC5HJ8GSB-01 |
|  TC58NC6623G6F |  TC58NVG0S3AFT05 |  TC58NVG0S3EBAI4 |  TC58NVG0S3EBAI7 |  TC58NVG0S3EBAI7LRH |
|  TC58NVG0S3ETA00 |  TC58NVG0S3ETAIO |  TC58NVG0S3ETAIO |  TC58NVG0S3HBAI6 |  TC58NVG0S3HBAI6 |
|  TC58NVG0S3HTAI0 |  TC58NVG0S3HTAI0B4H |  TC58NVG1S3EBAI4 |  TC58NVG1S3EBAI5 |  TC58NVG1S3ETA00 |
|  TC58NVG1S3ETA00 |  TC58NVG1S3ETAIO |  TC58NVG1S3ETAIO |  TC58NVG1S3ETAIO |  TC58NVG1S3HBAI4 |
|  TC58NVG1S3HBAI4 |  TC58NVG1S3HBAI6 |  TC58NVG1S3HBAI6 |  TC58NVG1S3HTA00 |  TC58NVG1S3HTA00 |
|  TC58NVG2S0HTAI0 |  TC58NVG2S0HTAI0 |  TC58NVG2S3ETA00 |  TC58NVG2S5HBAI6 |  TC58NVG3S0FTA00B4H |
|  TC58NVG4D2ETAIO0 |  TC58NYG1S8HBAI6 |  TC58NYG2S3ETAIO |  TC58NYG2S3ETAIO |  TC58NYM9S3EBAI4 |

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

Copyright © 2019 YIC International Co., Limited